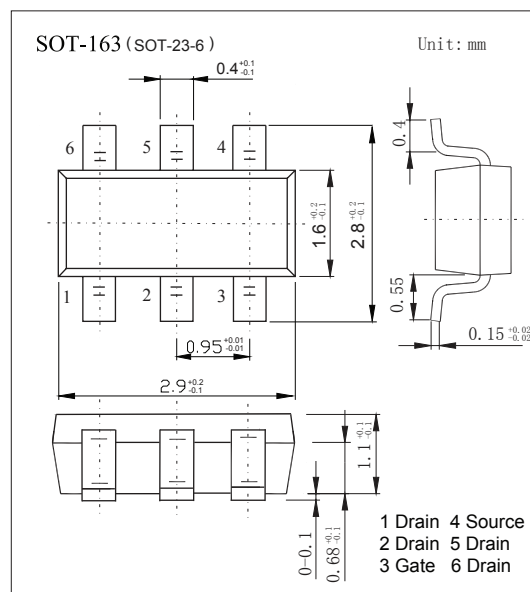
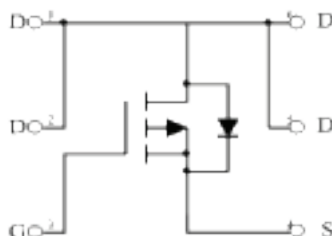


P Channel MOSFET

2SJ3053DV

■ Features

- Surface Mount Package
- Super High Density Cell Design
for Extremely Low $R_{DS(on)}$
- Exceptional On-resistance and Maximum
DC Current Capability

■ Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-150	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current (Note 1)	I_D	-1.4	A
Pulsed Drain Current ($t_p=10\mu\text{s}$)	I_{DM}	-5	
Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction- to-Ambient (Note 1)	R_{thJA}	357	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Junction Storage Temperature Range	T_{stg}	-55 to 150	
Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	T_L	260	

Note 1.Surface mounted on FR4 board using the minimum recommended pad size.

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■ Electrical Characteristics ($T_a = 25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =-250μA, V _{GS} =0V	-150			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-120V, V _{GS} =0V			-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Gate Threshold Voltage (Note 2)	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-2		-3	V
Static Drain-Source On-Resistance (Note 2)	R _{DS(on)}	V _{GS} =-10V, I _D =-1.4A			800	mΩ
		V _{GS} =-6V, I _D =-1A			850	
Forward Transconductance (Note 2)	g _{FS}	V _{DS} =-10V, I _D =-1.4A		4.5		S
Diode Forward Voltage	V _{SD}	I _S =-1A,V _{GS} =0V			-1.2	V
Dynamic Characteristics (Note 4)						
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =-50V, f=1MHz		520		pF
Output Capacitance	C _{oss}			30		
Reverse Transfer Capacitance	C _{rss}			20		
Switching Characteristics (Note 3, 4)						
Total Gate Charge	Q _g	V _{GS} =-6V, V _{DS} =-75V, I _D =-1A		10	15	nC
Gate Source Charge	Q _{gs}			2.5		
Gate Drain Charge	Q _{gd}			5		
Turn-On Delay Time	t _{d(on)}	V _{GEN} =-10V,V _{DD} =-75V, R _L =75Ω, I _D =-1A,R _G =1Ω		10	20	ns
Turn-On Rise Time	t _r			12	25	
Turn-Off Delay Time	t _{d(off)}			30	60	
Turn-Off Fall Time	t _f			12	25	

Note 2. Pulse Test : Pulse width=300 μs , duty cycle $\leq 2\%$.

3. Switching characteristics are independent of operating junction temperature.

4. Granted by design, not subject to producing.

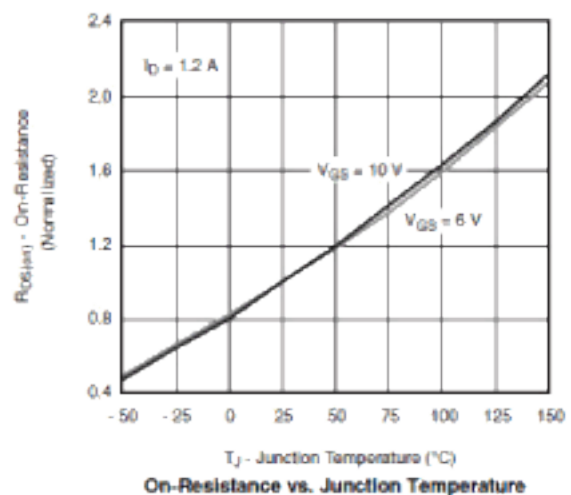
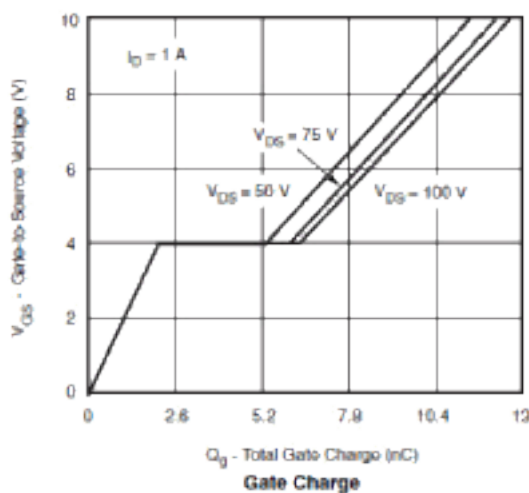
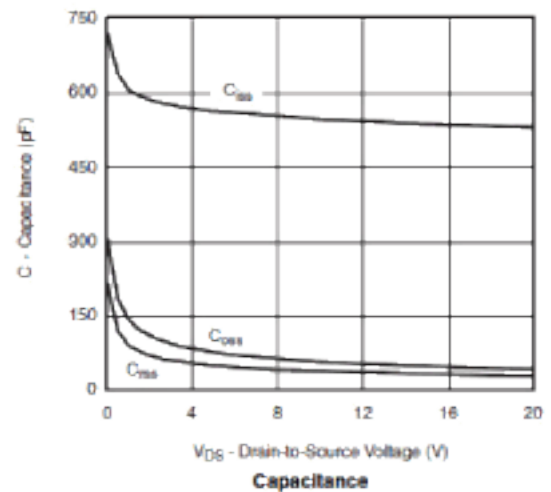
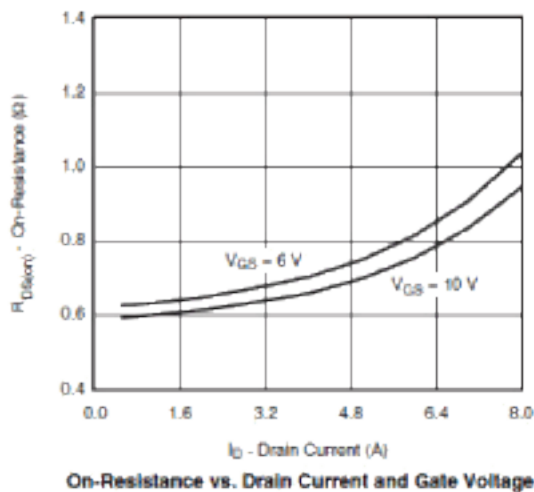
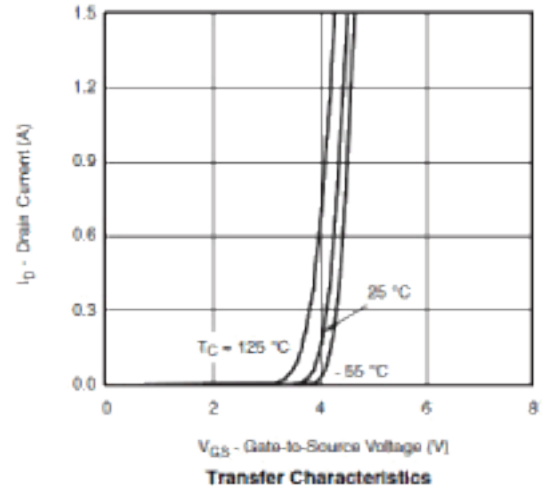
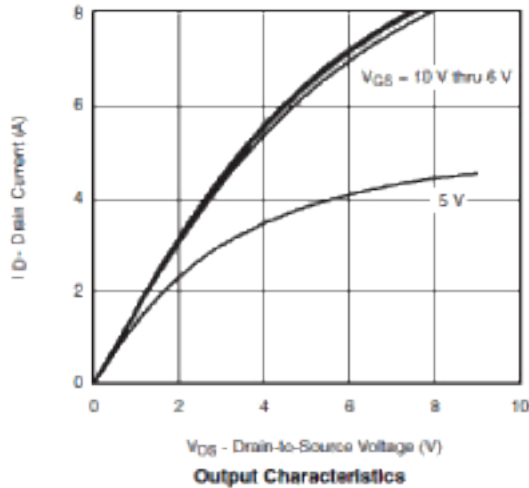
■ Marking

Marking	39W**
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P Channel MOSFET

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■ Typical Characteristics



P Channel MOSFET

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